

# MDU1931VRH

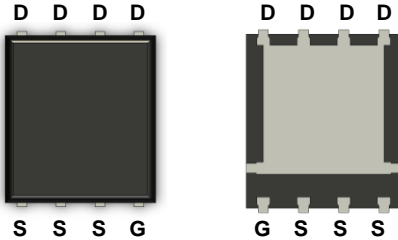
## Single N-channel Trench MOSFET 80V, 100A, 3.6mΩ

### General Description

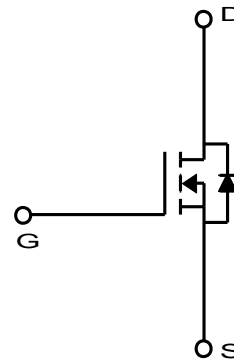
The MDU1931VRH uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU1931VRH is suitable device for Synchronous Rectification For Server and general purpose applications.

### Features

- $V_{DS} = 80V$
- $I_D = 100A @ V_{GS} = 10V$
- $R_{DS(ON)} < 3.6m\Omega @ V_{GS} = 10V$
- 100% UIL Tested
- 100% Rg Tested



PDFN56



### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	80	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$T_C=25^\circ C$ (Silicon Limited)	$I_D$	127.2	A
	$T_C=25^\circ C$ (Package Limited)		100.0	
	$T_C=100^\circ C$		80.5	
	$T_A=25^\circ C^{(3)}$		20.5 <sup>(3)</sup>	
Pulsed Drain Current		$I_{DM}$	400.0	
Power Dissipation	$T_C=25^\circ C$	$P_D$	96.2	W
	$T_C=100^\circ C$		38.5	
	$T_A=25^\circ C^{(3)}$		2.5 <sup>(3)</sup>	
Single Pulse Avalanche Energy <sup>(2)</sup>		$E_{AS}$	242	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	°C

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.3	

## Ordering Information

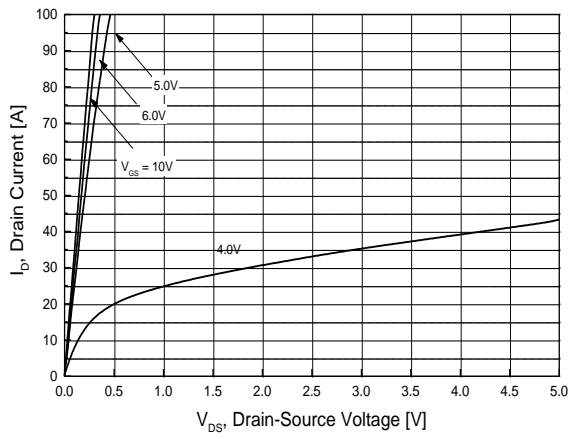
Part Number	Temp. Range	Package	Packing	RoHS Status
MDU1931VRH	-55~150°C	PDFN56	Tape & Reel	Halogen Free

## Electrical Characteristics (T<sub>J</sub> = 25°C)

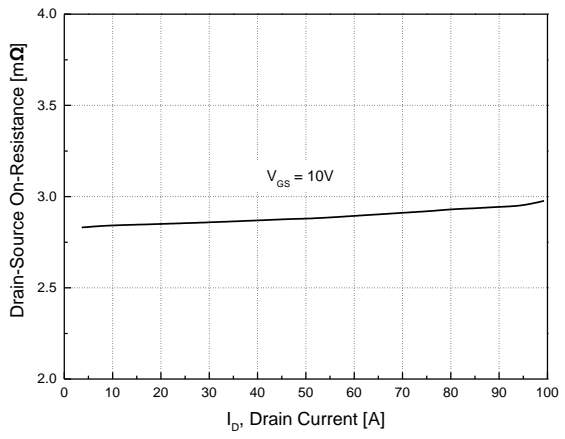
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	80	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 72V, V <sub>GS</sub> = 0V	-	-	1.0	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±0.1	
Drain-Source ON Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A	-	2.9	3.6	mΩ
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 50A	-	80.0	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g(10.0V)</sub>	V <sub>DS</sub> = 40.0V, I <sub>D</sub> = 50.0A, V <sub>GS</sub> = 10V	-	68.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	18.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	15.7	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 40.0V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	4,630	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	40	-	
Output Capacitance	C <sub>oss</sub>		-	1,050	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 40.0V, I <sub>D</sub> = 50A, R <sub>G</sub> = 3.0Ω	-	19.6	-	ns
Rise Time	t <sub>r</sub>		-	41.0	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30.3	-	
Fall Time	t <sub>f</sub>		-	18.9	-	
Gate Resistance	R <sub>g</sub>	f=1 MHz	-	2.0	-	Ω
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 50A, V <sub>GS</sub> = 0V	-	0.80	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50A, dI/dt = 100A/μs	-	60.0	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	110.0	-	nC

Note :

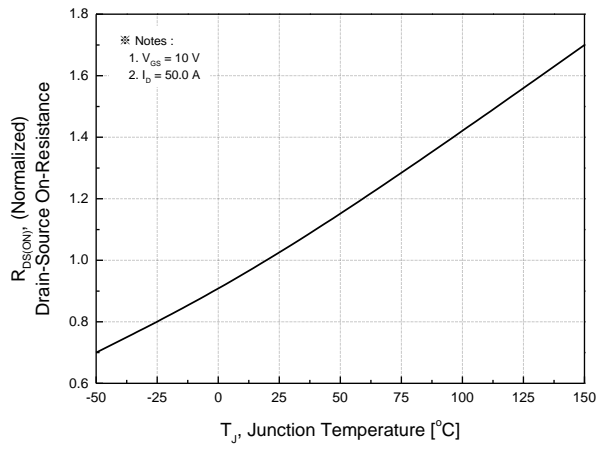
- The R<sub>thja</sub> was measured with the device mounted on 74.2 \* 74.2 mm<sup>2</sup> Copper buried FR4 board. The heat sink paddle size for the drain connection of device is 4.5 \* 6.0 mm<sup>2</sup>.
- E<sub>AS</sub> is tested at starting T<sub>J</sub> = 25°C, L = 1.0mH, I<sub>AS</sub> = 22.0A, V<sub>GS</sub> = 10V.
- T < 10sec.



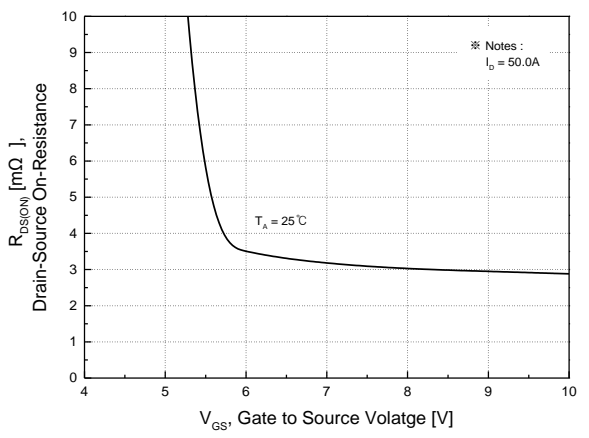
**Fig.1 On-Region Characteristics**



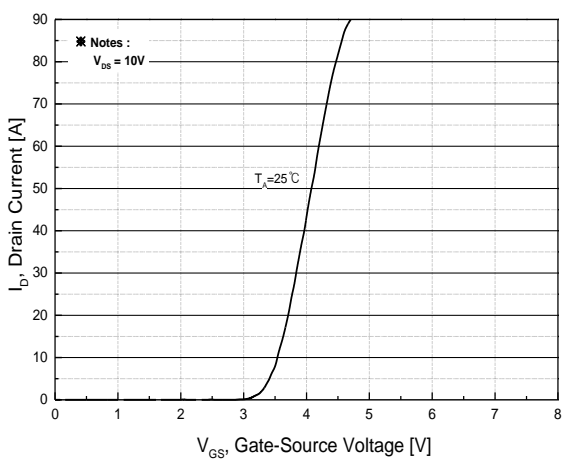
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



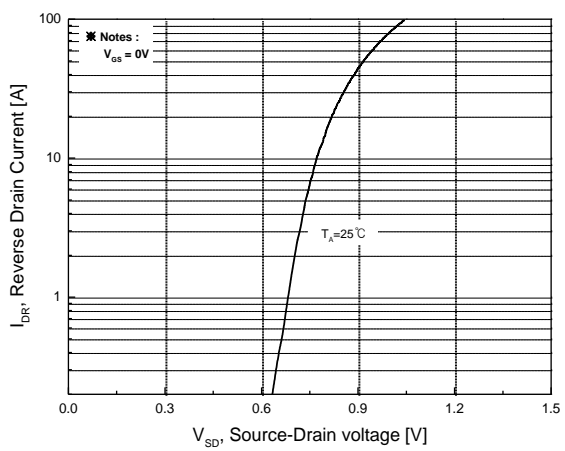
**Fig.3 On-Resistance Variation with Temperature**



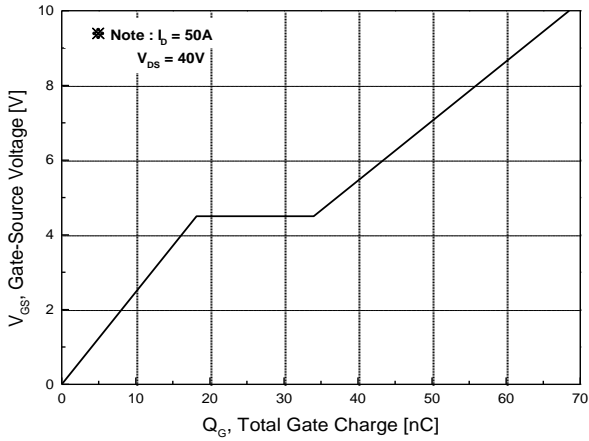
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



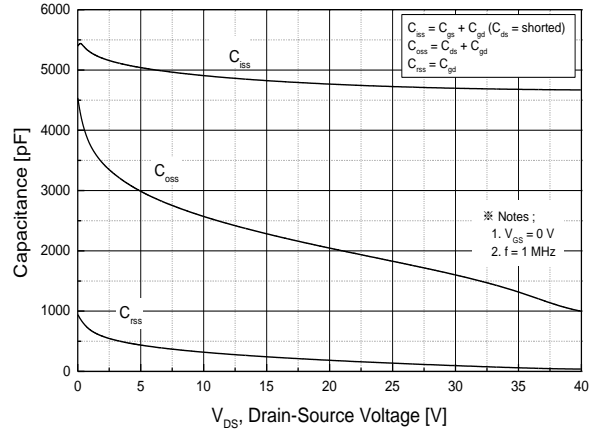
**Fig.5 Transfer Characteristics**



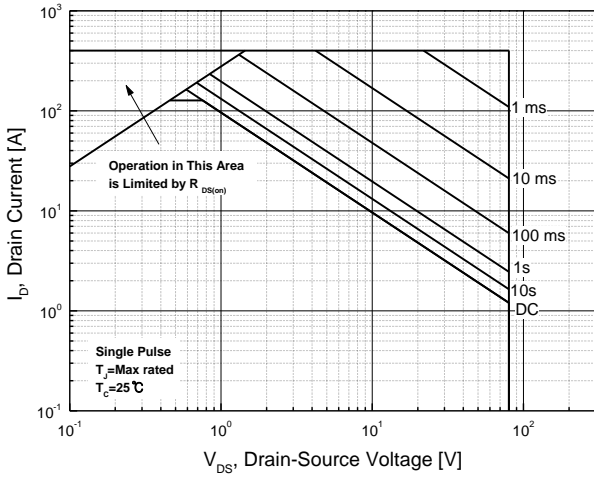
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



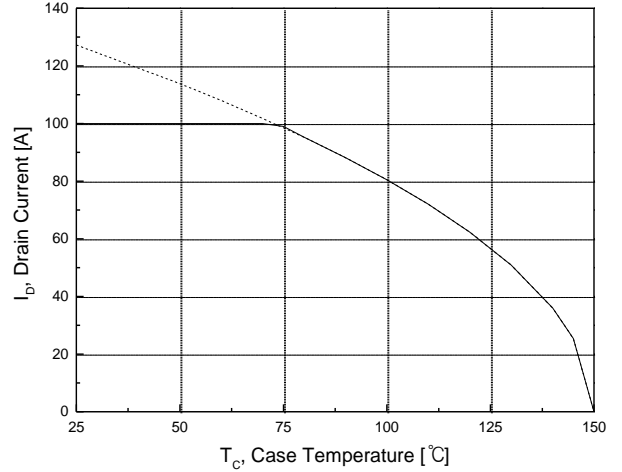
**Fig.7 Gate Charge Characteristics**



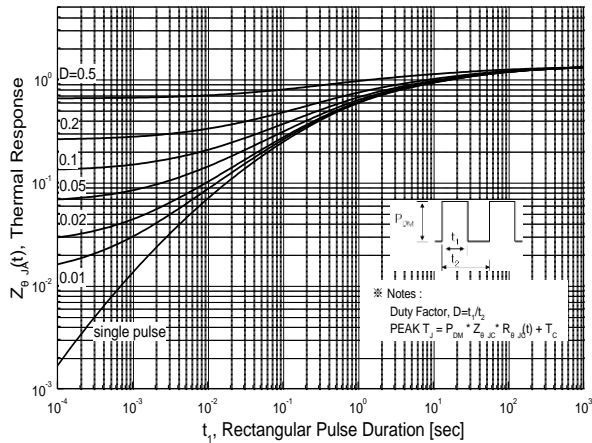
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Case Temperature**

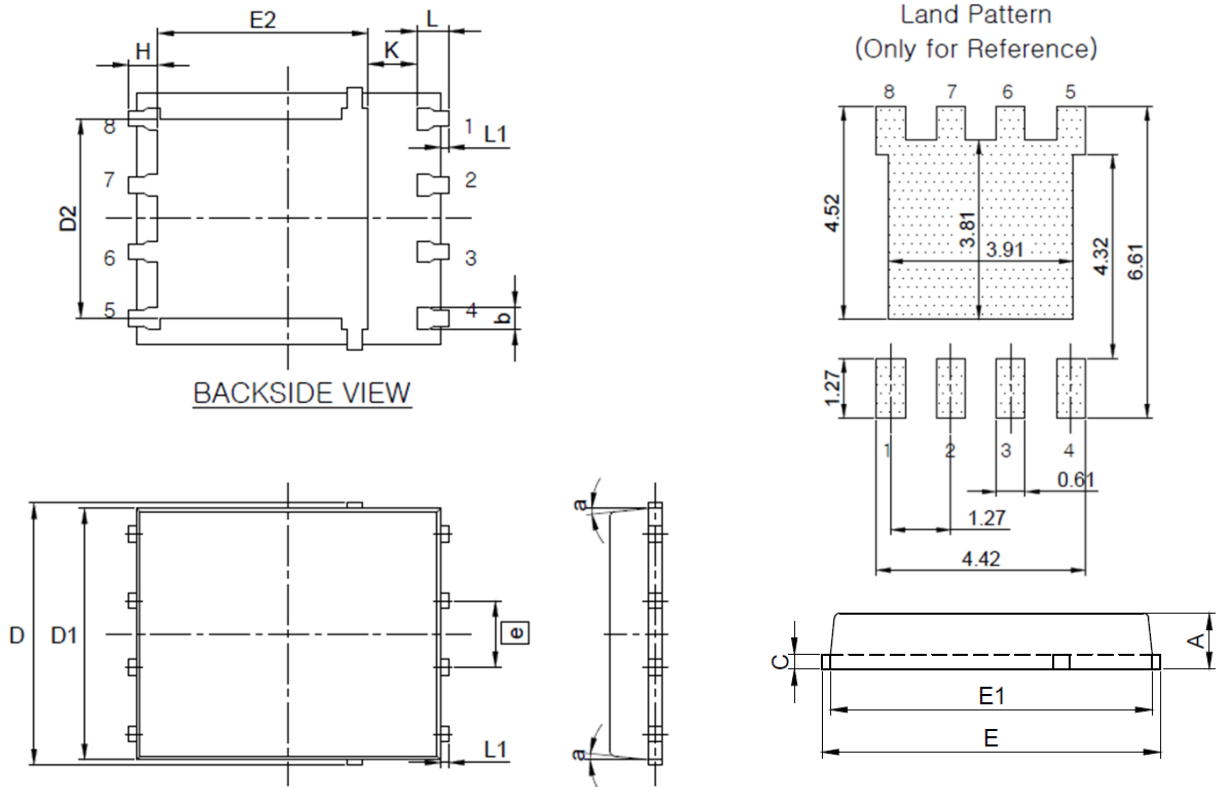


**Fig.11 Transient Thermal Response Curve**

## Package Dimension

### PDFN56 (5x6mm)

Dimensions are in millimeters, unless otherwise specified



Symbol	Dimension (mm)		
	Min	Nom	Max
A	0.90	-	1.10
b	0.33	-	0.51
C	0.20	-	0.34
D	4.50	-	5.30
D1	4.50	-	5.10
D2	3.61	-	4.22
E	5.90	-	6.30
E1	5.50	-	6.10
E2	3.38	-	4.30
e	1.27 BSC		
H	0.41	-	0.71
K	0.20	-	-
L	0.51	-	0.71
L1	0.06	-	0.20
a	0°	-	12°

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